

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
ATTY. DOCKET NO.
061282-0234SERIAL NO.
10/574,863APPLICANT
Yuichiro SASAKI, et al.

(Substitute for form 1449/PTO)

FILING DATE
April 06, 2006GROUP
2823**U.S. PATENT DOCUMENTS**

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	US	6,159,810	12-12-2000	YANG	
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		WO 03/014979 A	02-20-2003	APPLIED MATERIALS, INC.		X
		JP 2530990 B2	09-04-1996	FUJITSU LTD	Corresponds to US 5,407,845	X
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
		International Search Report issued in International Patent Application No. PCT/JP2005/009949 dated July 5, 2005	
		International Search Report issued in International Patent Application No. PCT/JP2004015308 mailed January 18, 2005	
		Japanese Notification of Reasons for Refusal, w/ English translation thereof, issued in Japanese Patent Application No. JP 2005-502685 dated May 19, 2009	
		European Search Report issued in European Patent Application No. EP 04710478 dated May 12, 2009	
EXAMINER		DATE CONSIDERED 11/25/2009	
/George Fourson/			

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1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

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SHEET 2 OF 2

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